NSN 5962-01-372-6876

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Maximum Power Dissipation Rating:
1.2 watts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
End Application:
7p blk 2 dcn, e/i fscm 49956
Features Provided:
Programmable
Inclosure Material:
Ceramic
Inclosure Configuration:
Dual-in-line
Output Logic Form:
Complementary-metal oxide-semiconductor logic
Input Circuit Pattern:
22 input
Case Outline Source And Designator:
D-9 mil-m-38510
Current Rating Per Characteristic:
16.00 milliamperes reverse current, dc
Terminal Surface Treatment:
Solder
Product Name:
Microcircuit, memory, digital, cmos, one-time programmable array logic, monolithic silicon
Voltage Rating And Type Per Characteristic:
-2.0 volts absolute input and 7.0 volts absolute input
Time Rating Per Chacteristic:
20.00 nanoseconds af output megawatts
Memory Device Type:
Pal
Hybrid Technology Type:
Monolithic
Special Features:
One-time programmable only
Test Data Document:
81349-mil-m-38510 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification
format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain
environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). And 96906-mil-std-883
standard (includes industry or association standards, individual manufactureer standards, etc.).
Terminal Type And Quantity:

67269 E062 99670 government standard

24 printed circuit

Specification Data:

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Specification Or Standard:

04 type and I case and a finish

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

A458a0